

Description

This bipolar junction transistor (BJT) is designed to meet the stringent requirements of automotive applications.

Features

- BV_{CEO} > -60V
- I_C = -5.5A High Continuous Collector Current
- I_{CM} = -15A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < -70mV @ -1A
- $R_{SAT} = 39m\Omega$ for a Low Equivalent On-Resistance
- hFE Specified Up to -10A for a High Gain Hold Up
- Complementary NPN Type: ZX5T851GQ
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- The ZX5T951GQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

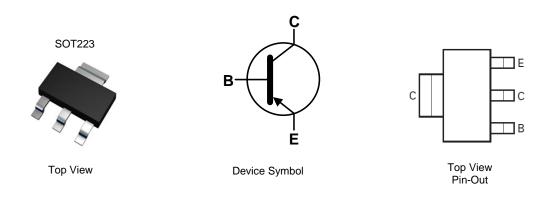
https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 (€3)
- Weight: 0.112 grams (Approximate)

Applications

- DC-DC Converters
- MOSFET & IGBT Gate Drivers
- Charging Circuits
- Power Switches
- Motor Control



Ordering Information (Note 4)

Notes:

Product	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZX5T951GQTC	X5T951	13	12	4000

1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

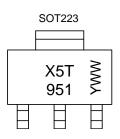
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



Marking Information



X5T 951 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 0= 2020) WW or $\overline{W}W$ = Week Code (01~53)

Absolute Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-100	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-5.5	A
Peak Pulse Current	I _{CM}	-15	A

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)		3.0 24		
Linear Derating Factor	(Note 6)	PD	1.6 12.8	mW /°C	
Thermal Resistance, Junction to Ambient	(Note 5)	R _θ JA	42		
memai Resistance, Junction to Ambient	(Note 6)	$R_{ extsf{ heta}JA}$	78	°C/W	
Thermal Resistance Junction to Lead	(Note 7)	$R_{\theta JL}$	10.48		
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C		

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 5. For a device surface mounted on 52mm x 52mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

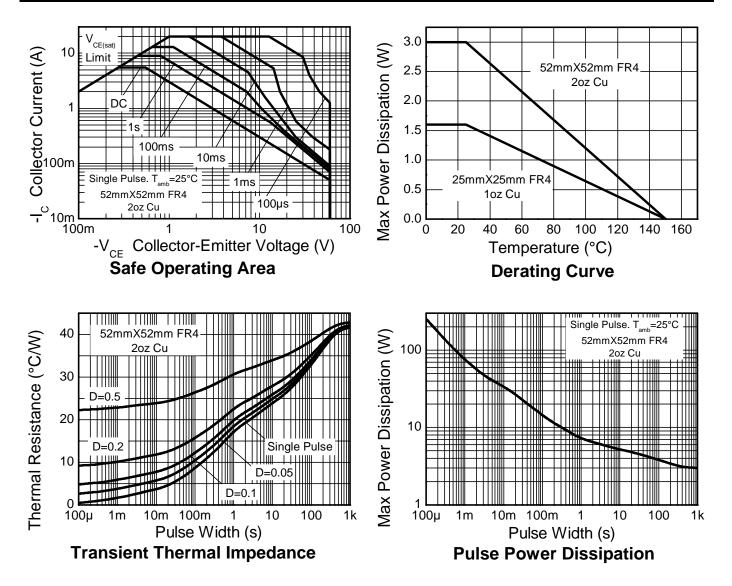
6. Same as Note 5 except the device is surface mounted on 25mm x 25mm with 1oz copper.

7. Thermal resistance from junction to solder-point (at the end of the collector lead).

8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





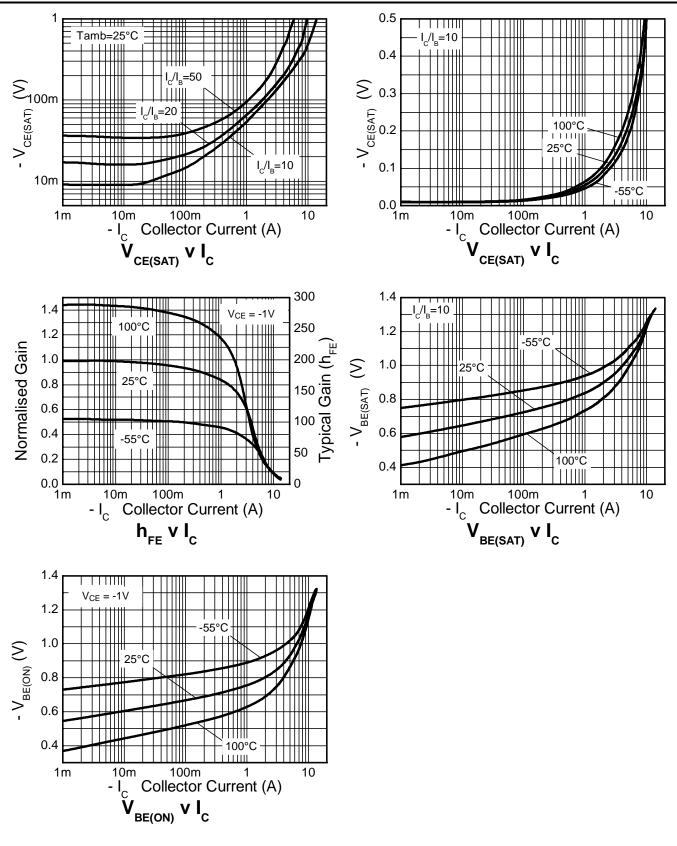
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-100	-120	_	V	I _C = -100μA
Collector-Emitter Breakdown Voltage	BV _{CER}	-100	-120	_	V	I _C = -1μA, RB ≤ 1kΩ
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-60	-80	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BVEBO	-7	-8.1	_	V	I _E = -100μA
Collector-Base Cutoff Current	I _{CBO}	—	<-1 —	-20 -0.5	nA μA	V _{CB} = -80V V _{CB} = -80V, T _A = +100°C
Collector-Emitter Cutoff Current	l _{CER} R ≤ 1kΩ	-	<-1 —	-20 -0.5	nA μA	V _{CB} = -80V V _{CB} = -80V, T _A = +100°C
Emitter Cutoff Current	I _{EBO}	—	<-1	-10	nA	V _{EB} = -6V
	hFE	100	250	_	_	I _C = -10mA, V _{CE} = -1V
Static Forward Current Transfer Ratio (Note 9)		100	200	300		$I_{C} = -2A, V_{CE} = -1V$
Static Forward Current Transfer Ratio (Note 9)		45	90	_		$I_{C} = -5A, V_{CE} = -1V$
		10	25	_		$I_{C} = -10A, V_{CE} = -1V$
	V _{CE(sat)}	—	-15	-25	mV	I _C = -100mA, I _B = -10mA
Collector Emitter Seturation Voltage (Note 0)		—	-55	-70		I _C = -1A, I _B = -100mA
Collector-Emitter Saturation Voltage (Note 9)		—	-90	-120		I _C = -2A, I _B = -200mA
		—	-195	-250		I _C = -5A, I _B = -500mA
Base-Emitter Saturation Voltage (Note 9)	V _{BE(sat)}	_	-1030	-1150	mV	I _C = -5A, I _B = -500mV
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(on)}	_	-920	-1020	mV	$I_{C} = -5A, V_{CE} = -1V$
Output Capacitance (Note 9)	C _{obo}	_	48		pF	V _{CB} = -10V, f = 1MHz
Transition Frequency	f _T	—	120	_	MHz	V _{CE} = -10V, I _C = -100mA f = 50MHz
Switching Time	t _{on}	—	39		ns	$V_{CC} = -10V, I_{C} = -1A$
	t _{off}	_	370	_	115	$I_{B1} = -I_{B2} = -100 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



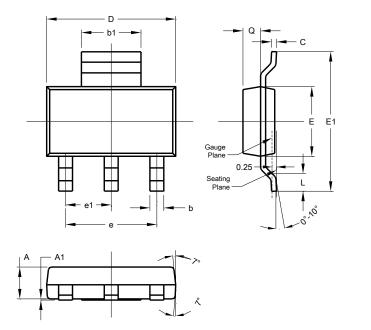
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)





Package Outline Dimensions

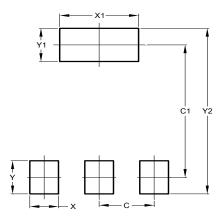
Please see http://www.diodes.com/package-outlines.html for the latest version.



	SOT223					
Dim	Min	Max	Тур			
Α	1.55	1.65	1.60			
A1	0.010	0.15	0.05			
b	0.60	0.80	0.70			
b1	2.90	3.10	3.00			
С	0.20	0.30	0.25			
D	6.45	6.55	6.50			
Е	3.45	3.55	3.50			
E1	6.90	7.10	7.00			
е	-	-	4.60			
e1	-	-	2.30			
L	0.85	1.05	0.95			
Q	0.84	0.94	0.89			
All [All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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